DPS2009 Program (September 24)

Session	No.	Title	Author	Affiliation
<<Plenary>> 9:00 - 9:40, 205(C)		Development of Large Area Materials Processing Technologies: High Frequency CCPs for Microelectronics to Web Processing of Polymers	Y. Yang	Univ. of Michigan
			M. Wang	Univ. of Michigan
			J. Shoeb	Univ. of Michigan
			M.J. Kushner	Univ. of Michigan
Break				
Award Ceremony 9:50 - 10:05, M201(D) [Presenter: T. Ohiwa]				
Session 1 New technologies for plasma control 10:10 - 11:20, M201(D) [Chair: M. Sekine]	1-1	Effects of Inductively Coupled Plasma and Substrate Control Parameters on 193 nm Photoresist Roughening	M. J. Titus	Univ. of California, Berkeley
			D. B. Graves	Univ. of California, Berkeley
	1-2	Analysis of Plasma-Wall Reactions using Virtual OES Signal during Dielectric Etching	N. Kuboi	Sony corp.
			M. Fukasawa	Sony corp.
			A. Kawashima	Sony corp.
			K. Oshima	Sony corp.
			K. Nagahata	Sony corp.
			T. Tatsumi	Sony corp.
	1-3	<Invited> EEDf of the DC+RF Hybrid and its Effects on Etching Process	L. Chen	Tokyo Electron America, Inc.
			L. Xu	Tokyo Electron America, Inc.
			M. Funk	Tokyo electron America, Inc.
Break				
Session 2 Poster session (1) 11:30 - 13:30 [Chair: H. Hayashi, T. Shirafuji]	2-P	<Poster> Plasma & Surface Reactions; Conductor & Si Etching; Modeling and Simulation; Plasma Equipment and Monitoring System; CVD/PVD/ALD		
Lunch				
<<Plenary>> 14:00 - 14:40, 205(C)		Vacuum Ultraviolet Plasma Emission in a Dielectric Etch Reactor	E. Hudson	Lam Research Corp.
			M. Moravej	Lam Research Corp.
			M. Block	Lam Research Corp.
			S. Sirard	Lam Research Corp.
			D. Wei	Lam Research Corp.
			K. Takeshita	Lam Research Corp.
			B. Jinnai	Tohoku Univ.
			S. Samukawa	Tohoku Univ.
Break				
Session3 "Arranged session" Precise Control of Plasma-surface reactions (1) 14:50 - 16:00, M201(D) [Chair: N. Itabashi]	3-1	<Invited> Nanoprocessing with Cluster Beams—Challenges and Opportunities	J. Matsuo	Kyoto University, CREST
	3-2	Determination of Precursors for Nitriding Silicon Surface using Inductively-Coupled Nitrogen Plasma	Y. Horikawa	Nagoya Univ.
			K. Kurihara	Toshiba Corp.
			K. Sasaki	Nagoya Univ.
	3-3	Optical and Electrical Characterization of H2 Plasma-Damaged Si Surface Structures and its Impact on In-line Monitoring	Y. Nakakubo	Kyoto Univ.
			A. Matsuda	Kyoto Univ.
			M. Fukasawa	Sony Corp.
			Y. Takao	Kyoto Univ.
			T. Tatsumi	Sony Corp.
			K. Eriguchi	Kyoto Univ.
			K. Ono	Kyoto Univ.
Break				
Session4 "Arranged session" Precise Control of Plasma-surface reactions (2) 16:20 - 17:20, M201(D) [Chair: I. Sawada]	4-1	Low Damage Resist Strip for Porous SiOCH using 100 MHz / 13.56 MHz DFS CCP	T. Imamura	Toshiba Corp.
			K. Yamamoto	Toshiba Corp.
			K. Sato	Toshiba Corp.
			K. Kurihara	Toshiba Corp.
			H. Hayashi	Toshiba Corp.
			T. Ohiwa	Toshiba Corp.
	4-2	In-situ Evaluation of H2 Plasma Damage on Porous SiOCH Low-k Films	H. Yamamoto	Nagoya Univ.
			K. Takeda	Nagoya Univ.
			M. Sekine	Nagoya Univ.
			M. Hori	Nagoya Univ.
			T. Kaminatsui	Toshiba Corp.
			K. Yamamoto	Toshiba Corp.
			H. Hayashi	Toshiba Corp.
			I. Sakai	Toshiba Corp.
			T. Ohiwa	Toshiba Corp.
	4-3	Wiggling of Porous Dielectric Lines for Advanced Technological Node: from Simulation to Experiment	J. Ducote	STMicroelectronics
			T. David	CEA-LETI-Minatec
			N. Posseme	CEA-LETI-Minatec
			T. Chevolleau	CNRS-LTM
			F. Bailly	STMicroelectronics
			A. Ostrovsky	STMicroelectronics
			M. Guillermet	CEA-LETI-Minatec
			C. Verove	STMicroelectronics
			J.C. Barbe	CEA-LETI-Minatec
			R.L. Inglebert	CNRS-LTM
			O. Joubert	CNRS-LTM
Break				
Session 5 Poster session (2) 17:30 - 19:30 [Chair: S. Miyazaki, K. Takahashi]	5-P	<Poster> Dielectric Etching; Plasma Diagnostics; Plasma processes for 3D Devices, FPD, LED, LASER, Organic Devices, Bio-Application, Medicine, MEMS, Nanotechnologies, and Environmental Technology; Processes using Atmospheric and Liquid Plasmas; New Dry Process Concept; Wet Process and Reactions		

DPS2009 Program (September 25)

Session	No.	Title	Authors	Affiliation
<<Plenary>> 9:00 - 9:40, 205(C) [Chair: M. Nakamura]		Three-Dimensional Integration Technology Using Self-Assembly Technique	M. Koyanagi	Tohoku Univ.
Break				
Session 6 More Moore & More than Moore 9:50 - 11:20, M201(D) [Chair: K. Kinoshita]	6-1	Role of Radical Reaction in Non-Bosch TSV Etching	T. Maruyama T. Narukage R. Onuki K. Yonekura N. Fujiwara	Renesas Technology Corp. Renesas Semiconductor Engineering Corp. Renesas Technology Corp. Renesas Technology Corp. Renesas Technology Corp.
	6-2	Dry-Etch Fin Patterning on SOI: Transition from 32 to 22nm Node on a 6T-SRAM Cell	E. Altamirano-Sanchez M. Ercken A. Veloso M. Demand W. Boullart	imec imec imec imec imec
	6-3	Advanced Gate Dimension Control for R2R Loop Implementation in an Industrial Environment	L. Babaud P. Gouraud E. Pargon O. Joubert	ST Microelectronics/LTM,CNRS ST Microelectronics LTM,CNRS LTM,CNRS
	6-4	<Invited> Multi-layer Stacking Technology using Direct Connection between TSV and Bump	N. Miyakawa E. Hashimoto T. Maebashi N. Nakamura Y. Sacho, S. Nakayama S. Toyoda	Honda Research Inst. Japan Co. Honda Research Inst. Japan Co. Honda Research Inst. Japan Co. Honda Research Inst. Japan Co. Honda Research Inst. Japan Co. Honda Research Inst. Japan Co. Honda Research Inst. Japan Co.
Break				
Session 7 "Arranged session" Precise Control of Plasma-surface reactions (3) 11:40 - 13:00, M201(D) [Chair: K. Kurihara]	7-1	Analyses of Surface Reaction on Cellulose and Gycine Treated in Atmospheric Microwave-Excited Plasmas for Elucidating the Mechanism of Sterilization	S. Yoshida T. Ogawa T. Fukuda K. Takahashi T. Urayama S. Aoki	Kyoto Inst. Tech. Kyoto Inst. Tech. Kyoto Inst. Tech. Kyoto Inst. Tech. Adtec Europe Adtec Plasma Tech.
	7-2	Growth of the SiN Nanoparticles by using Plasma Etching and the Application for the Solar Cells	C. Yang S.-H. Ryu W.-J. Yoo Y.-J. Park J. M. Kim	Sungkyunkwan Univ., SAINT Sungkyunkwan Univ., SAINT Sungkyunkwan Univ., SAINT Samsung Advanced Inst. of Technology Samsung Advanced Inst. of Technology
	7-3	Etching Magnetic Tunnel Junction with Metal Etchers	K. Kinoshita H. Utsumi K. Suemitsu H. Hada T. Sugibayashi	NEC Corp. NEC Corp. NEC Corp. NEC Corp. NEC Corp.
	7-4	Formation of Cobalt and Cobalt-Slicide Nanodots on ultrathin SiO2 Induced by Remote Hydrogen Plasma	A. Kawanami K. Makihara M. Ikeda S. Miyazaki	Hiroshima Univ. Hiroshima Univ. Hiroshima Univ. Hiroshima Univ.
Lunch				
<<Plenary>> 14:00 - 14:40, 205(C) [Chair: T. Ohiwa]		Innovative Technologies for New Semiconductor Era	C.-J. Kang Y.-J. Kim K.-S. Shin	Samsung Electronics CO., LTD Samsung Electronics CO., LTD Samsung Electronics CO., LTD
Break				
Session 8 Advanced dry etching systems 14:50 - 16:00, M201(D) [Chair: K. Nojiri]	8-1	<Invited> Three-dimensional Modeling of Plasma Processing Equipment	S. Rauf J. Kenney Z. Chen K. Collins	Applied Materials, Inc. Applied Materials, Inc. Applied Materials, Inc. Applied Materials, Inc.
	8-2	Tilting Control at Wafer Edge by Biasing to Focus Ring in UHF-ECR Dielectric Etching Apparatus	K. Maeda K. Yokogawa T. Ichino T. Tamura K. Hirozane T. Kanekiyo M. Izawa	Hitachi Ltd. Hitachi Ltd. Hitachi High-Technologies Hitachi High-Technologies Hitachi High-Technologies Hitachi High-Technologies Hitachi Ltd.
	8-3	Fine Ion Energy Control for Sub-32 nm Node Device RIE using Pulsed-DC Superimposed 100 MHz rf CCP	H. Hayashi A. Ui T. Kaminatsui K. Yamamoto K. Kikutani I. Sakai T. Ohiwa	Toshiba Corp. Toshiba Corp. Toshiba Corp. Toshiba Corp. Toshiba Corp. Toshiba Corp. Toshiba Corp.
Break				
Session 9 Damage & Fluctuation 16:20 - 17:40, M201(D) [Chair: H. Kokura]	9-1	Formation of High Quality SiO2 and SiO2/Si Interface using Thermal Plasma Jet Induced Millisecond Annealing and Post-Metallization Annealing	Y. Hiroshige S. Higashi K. Matsumoto S. Miyazaki	Hiroshima Univ. Hiroshima Univ. Hiroshima Univ. Hiroshima Univ.
	9-2	Linewidth Roughness Transfer during Gate Stack Patterning with Amorphous Carbon Mask: Impact of Cure and Trim Processes	E. Pargon L. Azarnouche M. Martin O. Luere K. Menguelti P. Gouraud O. Joubert	LTM/CNRS STMicroelectronics LTM/CNRS LTM/CNRS LTM/CNRS STMicroelectronics LTM/CNRS
	9-3	Investigation of Mask Distortion during Trimming	N. Kofuji H. Miura	Hitachi, Ltd. Tohoku Univ.
	9-4	Threshold Voltage Instability Induced by Plasma Process Damage in Advanced MOSFETs	K. Eriguchi Y. Nakakubo A. Matsuda M. Kamei Y. Takao K. Ono	Kyoto Univ. Kyoto Univ. Kyoto Univ. Kyoto Univ. Kyoto Univ. Kyoto Univ.

Closing Remark 17:40 - 17:50, M201(D) [N. Itabashi]

DPS2009 Program (Poster presentations)

Poster session (1)

(9/24) 11:30 - 13:30

[Chair: H. Hayashi, T. Shirafuji]

Category	No.	Title	Authors	Affiliations
Plasma & Surface Reactions	2-P01	Cylinder Rod Surface Coating using Sputtering Deposition Method with Modulated Magnetic Field	H. Kawasaki K. Shibahara T. Ohshima Y. Yagyu Y. Suda	Sasebo National College of Technology Sasebo National College of Technology Sasebo National College of Technology Sasebo National College of Technology Sasebo National College of Technology
	2-P02	Investigation of the Scalability of TiN Barrier Layer for Advanced Si-Processing	G. Zhang W.J. Yoo	Sungkyunkwan Univ. Sungkyunkwan Univ.
	2-P03	Chemical Sputtering of Chlorinated GaN	K. Harafuji K. Kawamura	Ritsumeikan Univ. Tokyo Inst. of Technology
	2-P04	Effect of Ar/O2 Ion-beam Treatment on the Interfacial Adhesion and Chemical Reaction between Sputter-deposited Cu film and FR-4 Substrate	K.-J. Min S.-C. Park G.-H. Lee K.-W. Lee J.-D. Kim D.-G. Kim Y.-B. Park	Andong National Univ. Andong National Univ. Korea Inst. of Materials Science Amkor Technology Korea Inc. Amkor Technology Korea Inc. Korea Inst. of Materials Science Andong National Univ.
	2-P05	Effect of Bonding Temperature and Post-Annealing Conditions on Cu-Cu Bonding Quality for 3-D IC Integration	E.-J. Jang J.-W. Kim B. Kim T. Matthias S. Hyun H.-J. Lee Y.-B. Park	Andong National Univ. Andong National Univ. EV Group EV Group Korea Inst. of Machinery & Materials Korea Inst. of Machinery & Materials Andong National Univ.
	2-P06	Reduction of Fluorinated Al2O3 by Irradiating H2 and O2 Plasmas	K. Miwa N. Takada K. Sasaki	Nagoya Univ. Nagoya Univ. Nagoya Univ.
	2-P07	Chamber Surface Control for Process Stability	Y. Chiba T. Matsumoto M. Terahara H. Kokura F. Harada A. Hasegawa	Fujitsu Microelectronics Ltd. Fujitsu Microelectronics Ltd. Fujitsu Microelectronics Ltd. Fujitsu Microelectronics Ltd. Fujitsu Microelectronics Ltd. Fujitsu Microelectronics Ltd.
	2-P08	Effects of Argon Plasma Surface Modification on Peel Strength of Woven Type Ultra High Molecular Weight Polyethylene	C.Y. Huang J.Y. Wu S.K. Lin C.S. Tsai K.N. Chen J.T. Yeh	Tatung Univ. Tatung Univ. Tatung Univ. Tatung Univ. Tamkang Univ. National Taiwan Univ. of Science and Technology
	2-P09	Effect of Surface Roughness on Secondary Electron Emission of Diamond in Ne Plasma	T. Misu S. Ono M. Goto T. Arai	Kanagawa Inst. of Technology Kanagawa Inst. of Technology Kanagawa Inst. of Technology Kanagawa Inst. of Technology
	2-P10	Investigation of Photoresist Surface Modified Layer by Fluorocarbon Ion Bombardment	T. Takeuchi M. Sekine H. Toyoda K. Takeda M. Hori S.-Y. Kang I. Sawada	Nagoya Univ. Nagoya Univ. Nagoya Univ. Nagoya Univ. Nagoya Univ. Tokyo Electron Ltd. Tokyo Electron Ltd.
	2-P11	Combinatorial Analysis of Plasma-Materials Interactions for Advanced R&D of Future Nano Devices	Y. Setsuhara K. Cho K. Takenaka M. Shiratani M. Sekine M. Hori	Osaka Univ., JST, CREST Osaka Univ., JST, CREST Osaka Univ., JST, CREST Kyushu Univ., JST, CREST Nagoya Univ., JST, CREST Nagoya Univ., JST, CREST
	2-P12	Preparation and Characteristics of 'Nafion-like' Plasma Polymerized Membrane	Z. Jiang X. Yu Y. Meng Z.-J. Jiang Y. Shi C. Corr R. Boswell C. Charles M. Nagatsu	Chinese Academy of Sciences Chinese Academy of Sciences Chinese Academy of Sciences Chinese Academy of Sciences Chinese Academy of Sciences Australian National Univ. Australian National Univ. Australian National Univ. Shizuoka Univ.
	2-P13	Dust Particles Formed owing to Interactions between H2 or D2 Helicon Plasmas and Graphite	H. Miyata S. Iwashita Y. Yamada K. Koga M. Shiratani	Kyushu Univ. Kyushu Univ. Kyushu Univ. Kyushu Univ. Kyushu Univ.
	2-P14	Nano-Surface Chemical Bonding States Analysis of Plasma-Exposed Polymers with Hard X-Ray Photoelectron Spectroscopy	Y. Setsuhara K. Cho M. Shiratani M. Sekine M. Hori E. Ikeitaga O. Nakatsuka S. Zaima	Osaka Univ., JST, CREST Osaka Univ., JST, CREST Kyushu Univ., JST, CREST Nagoya Univ., JST, CREST Nagoya Univ., JST, CREST JASRI Nagoya Univ. Nagoya Univ.
	2-P15	Modification for Adsorption Property of Active Carbon Surface Preliminarily Treated by Polyvinylalcohol using Microwave Cold Plasma	M. Ueshima E. Toda Y. Nakajima K. Sugiyama	Hachinohe National College of Technology Saitama Univ. Saitama Univ. Hachinohe National College of Technology
Conductor & Si Etching	2-P16	Inductively Coupled Plasma Reactive Ion Etching of Gallium Indium Zinc Oxide Thin Films in Cl2/Ar Gas Mix	D.Y. Lee Y.B. Xiao E.H. Kim C.W. Chung	Inha Univ. Inha Univ. Inha Univ. Inha Univ.
	2-P17	Improvement of Surface Roughness in SOI Wafer Fabrication using Cl2-based Neutral Beam Etching	T.H. Min J.K. Yeon B.J. Park S.K. Kang M.H. Jeon G.Y. Yeom	Sungkyunkwan Univ. Sungkyunkwan Univ. Sungkyunkwan Univ. Sungkyunkwan Univ. Sungkyunkwan Univ. Sungkyunkwan Univ.
	2-P18	FinFET Metal Gate Hi-k Etch for Sub-32nm Technology	G. Kamarthy G. Lo I. Orain Y. Kimura R. Deshpande Y. Yamaguchi C. Lee L. Braly	Lam Research Corp. Lam Research Corp. Lam Research Corp. Lam Research Corp. Lam Research Corp. Lam Research Corp. Lam Research Corp. Lam Research Corp.

Session	No.	Title	Author	Affiliation
	2-P19	Atomic-scale Cellular Model and Profile Simulation of Si Etching: Analysis of Profile Anomalies and Microscopic Uniformity	H. Tsuda	Kyoto Univ.
			M. Mori	Kyoto Univ.
			K. Eriguchi	Kyoto Univ.
			K. Ono	Kyoto Univ.
	2-P20	Metal Gate High-k Etch Challenges and Solutions	G. Kamarthy	Lam Research Corp.
			I. Orain	Lam Research Corp.
			Y. Kimura	Lam Research Corp.
			A. Kabansky	Lam Research Corp.
			A. Ozzello	Lam Research Corp.
			L. Braly	Lam Research Corp.
	2-P21	Large Area Negative Ion Source Based on Matrix ECR Cells for Fast Silicon Etching	E. Stamate	Technical Univ. of Denmark
			A. Lacoste	Universite Joseph Fourier
Modeling and Simulation	2-P22	Lateral Relation of Epitaxial Thin Film with Large Lattice Mismatch on Samples Prepared by YAG Laser Deposition	S. Kaneko	Kanagawa Ind. Tech. Center
			K. Akiyama	Kanagawa Ind. Tech. Center
			T. Ito	Kanagawa Ind. Tech. Center
			M. Yasui	Kanagawa Ind. Tech. Center
			M. Soga	Kanagawa Ind. Tech. Center
			Y. Hirabayashi	Kanagawa Ind. Tech. Center
			H. Funakubo	Tokyo Inst. of Technologu
			M. Yoshimoto	Tokyo Inst. of Technologu
	2-P23	Estimation of the Branching Ratios of Electron Impact Dissociation of Fluorocarbon Compounds	S.-Y. Kang	Tokyo Electron Ltd.
			I. Sawada	Tokyo Electron Ltd.
	2-P24	Modeling of Particle Growth in Pulsed PCVD Process for Preparation of High-Quality Thin Films	D.-J. Kim	Kangwon National Univ.
			T.D. Nguyen	Kangwon National Univ.
			K.-S. Kim	Kangwon National Univ.
Plasma Equipment and Monitoring System	2-P25	Development of High-Density Radio Frequency Plasma Source with Ring-Shaped Hollow Electrode for Dry Processing	Y. Ohtsu	Saga Univ.
			H. Urasaki	Saga Univ.
			T. Misawa	Saga Univ.
			H. Fujita	Saga Univ.
	2-P26	Investigation of the Inductively Coupled Plasma Source with a Ni-Zn Ferrite Module	G.H. Gweon	Sungkyunkwan Univ.
			K.N. Kim	Sungkyunkwan Univ.
			J.H. Lim	Sungkyunkwan Univ.
			S.P. Hong	Sungkyunkwan Univ.
			G.Y. Yeom	Sungkyunkwan Univ.
	2-P27	Polyimide Film Etching by an Atmospheric-Pressure μPlasma using a 100-μm-φ SUS Pipe	H. Yoshiki	Tsuruoka National College of Technology
	2-P28	Monitoring of Growth and Removal of Hydrocarbon Thin Films by Optical Reflectance Interference	K. Uehara	Nagasaki Univ.
			M. Shinohara	Nagasaki Univ.
			Y. Matsuda	Nagasaki Univ.
CVD/PVD/ALD	2-P29	Thin Film Transistors with Amorphous IGZO Semiconductor Fabricated by DC Magnetron Sputtering	W.-S. Kim	Hanyang Univ.
			Y.-K. Moon	Hanyang Univ.
			S. Lee	Hanyang Univ.
			B.-W. Kang	Hanyang Univ.
			K.-T. Kim	Hanyang Univ.
			J.-W. Park	Hanyang Univ.
	2-P30	Corrosion Properties of CrNTiN Multi-Coating on 316L Stainless Steel for Bipolar Plate in Polymer Electrolyte Membrane Fuel Cell Application	N. D. Nam	Sungkyunkwan Univ.
			J.S. Song	Sungkyunkwan Univ.
			J.G. Kim	Sungkyunkwan Univ.
	2-P31	Deposition of a Carbon Nanocomposite Film using Magnetron Sputtering	T. Tsutsumi	Nagoya Univ.
			N. Takada	Nagoya Univ.
			N. Nafarizal	Univ. Tun Hussein Onn Malaysia
			K. Sasaki	Nagoya Univ.
	2-P32	Selective Epitaxial Growth of Silicon for Vertical Diode Application and Its Practical Selectivity	K.-S. Lee	Sungkyunkwan Univ / Samsung Electronics
			S.-J. Park	Samsung Electronics
			J.-J. Han	Samsung Electronics
			Y.-W. Hyung	Samsung Electronics
			S.-S. Kim	Samsung Electronics
			C.-J. Kang	Samsung Electronics
			J.-T. Moon	Samsung Electronics
			H.-S. Jeong	Samsung Electronics
			B.-D. Choi	Sungkyunkwan Univ
	2-P33	A Improvement Model For a Lower Leakage Current of Oxide-Nitride-Oxide (ONO) Inter-Poly Dielectrics Through Post Plasma Oxidation Treatment	W. Lee	Samsung Electronics / Univ. of Sungkyunkwan
			J. Jee	Samsung Electronics
			J. Bok	Samsung Electronics
			Y. Hyung	Samsung Electronics
			S. Kim	Samsung Electronics
			C.-J. Kang	Samsung Electronics
			J.-T. Moon	Samsung Electronics
			K.-S. Kim	Sungkyunkwan Univ
			Y. Roh	Sungkyunkwan Univ
	2-P34	Studies on the Characterization of Polystyrene Films Prepared by RF Plasma CVD Process	A.J. Choudhury	Inst. of Advanced Study in Sci. and Technol.
			J. Chutia	Inst. of Advanced Study in Sci. and Technol.
	2-P35	Fabrication of Tungsten Oxide Thin Film on the Flexible Substrate using RF Magnetron Sputtering in Ar/O2 Mixture Gas	T. Matsunaga	Sasebo National College of Technology
			T. Ohshima	Sasebo National College of Technology
			H. Kawasaki	Sasebo National College of Technology
			Y. Yagyu	Sasebo National College of Technology
			Y. Suda	Sasebo National College of Technology
	2-P36	Characterization of Double Interfaces System (Si3N4/SiO2/Si and SiO2/Si3N4/Si) Grown by ALD	S.K. Kang	Hanbat National Univ.
			S.K. Rha	Hanbat National Univ.
			J.H. Seo	Hanbat National Univ.
			Y.S. Lee	Hanbat National Univ.
			W.J. Lee	Sejong Univ.
	2-P37	Epitaxial Growth of b-FeSi2 Thin Film on SiC by Co-Sputtering of Iron and Silicon	K. Akiyama	Kanawaga Industrial Technology Center
			S. Kaneko	Kanawaga Industrial Technology Center
			T. Kadowaki	Kanawaga Industrial Technology Center
			Y. Hirabayashi	Kanawaga Industrial Technology Center
	2-P38	Growth of SnO2 Thick Films by Plasma Spray Physical Vapor Deposition	K. Iizuka	Univ. of Tokyo
			S. Sekiguchi	Univ. of Tokyo
			K. Nakamura	Uchiya Thermostat Corp.
			M. Kambara	Univ. of Tokyo
			T. Yoshida	Univ. of Tokyo
	2-P39	Preparation and Characterization of Copper Selenide and Indium Selenide Thin Films by MOCVD	J.H. Yoo	Sungkyunkwan Univ.
			S.M. Yu	Sungkyunkwan Univ.
			J.H. Lee	Sungkyunkwan Univ.
			C.H. Choi	LG Micron Ltd.
			J.B. Yoo	Sungkyunkwan Univ.
	2-P40	Pulsed Supermagnetron Plasma CVD of Amorphous Carbon Nitride Films	H. Kinoshita	Shizuoka Univ.
			A. Yamaguchi	Shizuoka Univ.
	2-P41	Enhancement of the Sidewall Step Coverage of the Sputter-Deposited Film Through the Ideally-Tapered Via	C.G. Kim	KAIST
			W.J. Lee	KAIST
	2-P42	Fabrication of CuInSe2 Thin Film by Metal-Organic Chemical Vapor Deposition	S.M. Yu	Sungkyunkwan Univ.
			J.H. Yoo	Sungkyunkwan Univ.
			J.H. Lee	Sungkyunkwan Univ.
			C.-H. Choi	LG Micron Ltd.
			J.-B. Yoo	Sungkyunkwan Univ.
	2-P43	Effects of NH3 Plasma Pretreatment of Ta Substrate on Copper Seed Layer Formation by PE-ALD	D.-Y. Moon	Hanyang Univ.
			T.-S. Kim	Hanyang Univ.
			B.M. Kim	Hynix
			J.H. Kim	Hynix
			J.-W. Park	Hanyang Univ.
	2-P44	Effect of N2 Gas Flow Ratio in Plasma Enhanced Chemical Vapor Deposition with SiH4-NH3-N2-He Gas Mixture on Stress Relaxation of Silicon Nitride	T. Murata	Renesas Technology Corp.
			Y. Miyagawa	Renesas Technology Corp.
			M. Matsuura	Renesas Technology Corp.
			K. Asai	Renesas Technology Corp.

Session	No.	Title	Author	Affiliation
	2-P45	**Monosilane Dissociation Process in Microwave-Excited High-Density H2/SiH4 Plasma**	H. Asano	Nagoya Univ.
			H. Endo	Nagoya Univ.
			T. Ishijima	Nagoya Univ.
			H. Toyoda	Nagoya Univ.
	2-P46	**Porosity Control of Nano-particle Composite Porous Low Dielectric Films using Pulse RF Discharges with Amplitude Modulation**	S. Iwashita	Kyushu Univ.
			H. Miyata	Kyushu Univ.
			K. Koga	Kyushu Univ.
			H. Matsuzaki	Kyushu Univ.
			M. Shiratani	Kyushu Univ.
			M. Akiyama	AIST
	2-P47	**Pressure and Aspect Ratio Dependence of Deposition Profile of Carbon Films on Trench Substrates Deposited by Plasma CVD**	T. Nomura	Kyushu Univ..
			Y. Korenaga	Kyushu Univ..
			J. Umetsu	Kyushu Univ..
			H. Matsuzaki	Kyushu Univ..
			K. Koga	Kyushu Univ. / JST, CREST.
			M. Shiratani	Kyushu Univ. / JST, CREST.
			Y. Setsuhara	Osaka Univ. / JST, CREST.
			M. Sekine	Nagoya Univ. / JST, CREST.
			M. Hori	Nagoya Univ. / JST, CREST.
	2-P48	**Characterics of Preparation Metallic Nanodot by Organ-Metal Solution with Burning Method**	I. Muramoto	Sojo Univ.
			S. Aoqui	Sojo Univ.
			H. Kawasaki	Sasebo National College of Technology
			T. Oosima	Sasebo National College of Technology
			T. Uematsu	Tokyo Metropolitan Industrial Technology Research Inst.
	2-P49	**Growth of TiO2 Thin Films on Polypropylene Particles by PCVD Process**	H.C. Pham	Kangwon National Univ.
			D.-J. Kim	Kangwon National Univ.
			K.-S. Kim	Kangwon National Univ.
	2-P50	**Synthesis of Si Nanoparticles for Multiple Exciton Generation Solar Cells using Multi-Hollow Discharge Plasma CVD**	Y. Kawashima	Kyushu Univ.
			H. Sato	Kyushu Univ.
			K. Koga	Kyushu Univ.
			M. Shiratani	Kyushu Univ.
			M. Kondo	AIST
	2-P51	**Plasma-Enhanced ALD Oxide Film by Microwave RLSA**	Y. Osawa	Tokyo Electron Technology Development Inst., Inc.
			H. Ueda	Tokyo Electron Technology Development Inst., Inc.
			M. Horigome	Tokyo Electron Technology Development Inst., Inc.
			Y. Tanaka	Tokyo Electron Technology Development Inst., Inc.
			T. Nozawa	Tokyo Electron Technology Development Inst., Inc.
	2-P52	**Growth of Ultrananocrystalline Diamond/Amorphous Carbon Composite Films using a Coaxial Arc Plasma Gun**	K. Hanada	Kyushu Univ.
			T. Yoshitake	Kyushu Univ.
			Y. Nakagawa	Kyushu Univ.
			T. Yoshida	Kyushu Univ.
			R. Ohtani	Saga-LS
			H. Setoyama	Saga-LS
			E. Kobayashi	Saga-LS
			K. Sumitani	Saga-LS
			T. Okajima	Saga-LS
			K. Nagayama	Kyushu Univ.
	2-P53	**Measurements of Surface Temperature of a-Si:H Films in Silane Multi-Hollow Discharges with IR Thermometer**	H. Sato	Kyushu Univ.
			Y. Kawashima	Kyushu Univ.
			K. Nakahara	Kyushu Univ.
			K. Koga	Kyushu Univ.
			M. Shiratani	Kyushu Univ.
	2-P54	**Time-Resolved Optical Observation of Plasma Process in Ultrananocrystalline Diamond/Amorphous Carbon Composite Films Deposition with a Coaxial Arc Plasma Gun**	K. Hanada	Kyushu Univ.
			T. Nishiyama	Kyushu Univ.
			T. Yoshitake	Kyushu Univ.
			K. Nagayama	Kyushu Univ.
	2-P55	**Oxygen Gas Barrier Properties Related with Structure of Hydrogenated Amorphous Carbon Films by ICP-CVD**	S.-M. Baek	Nagoya Univ.
			T. Shirafuji	Nagoya Univ.
			S.-P. Cho	Nagoya Univ.
			N. Saito	Nagoya Univ.
			O. Takai	Nagoya Univ.

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[Chair: S. Miyazaki, K. Takahashi]

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Dielectric Etching	5-P01	**Mechanism of Surface Roughening during Porous SiOCH Etching in Fluorocarbon Based Plasmas**	F. Bailly	STMicroelectronics
			T. David	CEA
			T. Chevolleau	CNRS
			N. Posseme	CEA
			O. Joubert	CEA
			C. Cardinaud	CNRS
	5-P02	**New Approach of Etching Analysis based on Internal Parameters in Combinatorial Plasma Process**	C.S. Moon	Nagoya Univ.
			K. Takeda	Nagoya Univ.
			M. Sekine	CREST, Nagoya Univ.
			Y. Setsuhara	CREST, Osaka Univ.
			M. Shiratani	CREST, Kyushu Univ.
			M. Hori	CREST, Nagoya Univ.
	5-P03	**TiO2 Etching by Atomic Layer Etching with BCl3 Gas and Ar Neutral Beam**	Y.Y. Kim	Sungkunkwan Univ.
			W.S. Lim	SAINT, Sungkyunkwan Univ.
			B.J. Park	Sungkunkwan Univ.
			G.Y. Yeom	Sungkunkwan Univ.
	5-P04	**Modification of Porous SiOCH Trench Sidewalls Induced by Reducing and Oxidizing Post Etching Plasma Treatments**	R. Bouyssou	CNRS-LTM
			T. Chevolleau	CNRS-LTM
			N. Posseme	CEA-LETI
			C. Licitra	CEA-LETI
			T. David	CEA-LETI
			A. Ostrovsky	STM
			C. Verove	STM
			O. Joubert	CNRS-LTM
	5-P05	**Use of RLSA Plasma and HBr Process to Achieve Zero CD-Bias and Pattern Density Independent Multi-layer Mask Etching**	T. Ozu	Tokyo Electron Development Inst.
			M. Sasaki	Tokyo Electron Development Inst.
			T. Nozawa	Tokyo Electron Development Inst.
	5-P06	**Etch Selectivity and Line Edge Roughness during Etching of Hard-Mask Layer with Patterned Extreme Ultra-Violet Resist in Dual-Frequency Capacitively Coupled Plasmas**	B.S. Kwon	Sungkyunkwan Univ.
			C.R. Jung	Sungkyunkwan Univ.
			W. Heo	Sungkyunkwan Univ.
			J.S. Park	Sungkyunkwan Univ.
			N.-E. Lee	Sungkyunkwan Univ.
			S.K. Lee	Hynix Semiconductor
	5-P07	**Damage-free Resist Ashing on Low-k Film Using Dual Frequency Capacitively Coupled Ar/O2 Plasma**	Y. Miyawaki	Nagoya Univ.
			K. Takeda	Nagoya Univ.
			M. Sekine	Nagoya Univ.
			M. Hori	Nagoya Univ.
Plasma Diagnostics	5-P08	**Collective Laser Thomson Scattering Diagnostics of Laser Produced Plasmas for EUV Light Sources**	K. Tomita	Kyushu Univ.
			Y. Hyakuta	Kyushu Univ.
			K. Ohara	Kyushu Univ.
			K. Uchino	Kyushu Univ.
	5-P09	**Application of a Grad-T Type Thermal Probe to the Discharge Plasma**	H. Matsuura	Osaka Prefecture Univ.
			K. Nakano	Osaka Prefecture Univ.
			S. Kado	Univ. of Tokyo
	5-P10	**The Multipole Resonance Probe- An Electromagnetic Approach**	M. Lapke	Ruhr-Univ. Bochum
			T. Mussenbrock	Ruhr-Univ. Bochum

Session	No.	Title	Author	Affiliation
			R.P. Brinkmann	Ruhr-Univ. Bochum
	5-P11	Absorption Measurement of Metal Atom Density in ICP Assisted Sputter-Deposition of Al-doped ZnO Thin Films	T. Iwata	Nagasaki Univ.
			R. Shindo	Nagasaki Univ.
			M. Shinohara	Nagasaki Univ.
			Y. Matsuda	Nagasaki Univ.
	5-P12	Emission Spectroscopy of Atmospheric Microplasma for Biomedical Application	M. Blajan	Shizuoka Univ.
			T. Ishii	Shizuoka Univ.
			M. Yamada	Shizuoka Univ.
			K. Shimizu	Shizuoka Univ.
	5-P13	Temporal Variation of Hydrogen Atom Spectrum Emitted from Pulsed Microwave Plasma under Atmospheric Pressure	H. Yang	Nagoya Univ.
			T. Ishijima	Nagoya Univ.
			H. Toyoda	Nagoya Univ.
	5-P14	Etching Characteristics and Mechanism of Ga-Doped ZnO Thin Films in Inductively Coupled HBr/Ar/CHF_3 Plasma	Y.-H. Ham	Korea Univ.
			A. Efremov	State Univ. of Chemistry &Technology
			H.-W. Lee	Hanseo Univ.
			S.J. Yun	Electronica and Telecommunications Research Inst.
			N.K. Min	Korea Univ.
			K.-H. Kwon	Korea Univ.
	5-P15	Model-Based Analysis of the Y_2O_3 Etching Mechanism in Inductively Coupled BCl_3/Ar and Cl_2/Ar Plasmas	M.-k. Kim	Korea Univ.
			A. Efremov	State Univ. of Chemistry & Technology
			H.W. Lee	Hanseo Univ.
			N.K. Min	Korea Univ.
			H.-H. Park	Yonsei Univ.
			K.-H. Kwon	Korea Univ.
	5-P16	Mircrowave Resonance Probes for Diagnostics of High Pressure Plasmas	K. Nakamura	Chubu Univ.
			J. Xu	Chubu Univ.
			Q. Zhang	Chubu Univ.
			H. Sugai	Chubu Univ.
	5-P17	Measurements of Electron Density in SiH_4+H_2 Multi-Hollow Discharges using a Frequency Shift Probe	K. Nakahara	Kyushu Univ.
			Y. Kawashima	Kyushu Univ.
			H. Sato	Kyushu Univ.
			K. Koga	Kyushu Univ.
			M. Shiratani	Kyushu Univ.
	5-P18	Laser Thomson Scattering Studies of Pulse Filament Discharges	K. Tomita	Kyushu Univ.
			Y. Yamagata	Kyushu Univ.
			K. Uchino	Kyushu Univ.
Plasma processes for 3D Devices, FPD, LED, LASER, Organic Devices, Bio-Application, Medicine, MEMS, Nanotechnologies, and Environmental Technology	5-P19	Hybrid White Organic Light-Emitting Diodes for Reduced Efficiency Roll-off	J.H. Seo	Hongik Univ.
			J.S. Park	Hongik Univ.
			J.R. Koo	Hongik Univ.
			B.M. Seo	Hongik Univ.
			K.H. Lee	Sungkyunkwan Univ.
			J.K. Park	Sungkyunkwan Univ.
			S.S. Yoon	Sungkyunkwan Univ.
			Y.K. Kim	Hongik Univ.
	5-P20	Modified Julolidine-Containing Emitters for Red Organic Light-Emitting Diodes	M.H. Park	Sungkyunkwan Univ.
			K.H. Lee	Sungkyunkwan Univ.
			S.M. Kim	Sungkyunkwan Univ.
			Y.K. Kim	Hongik Univ.
			S.S. Yoon	Sungkyunkwan Univ.
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			W.-S. Kim	Hanyang Univ.
			B.-W. Kang	Hanyang Univ.
			S. Lee	Hanyang Univ.
			J.-W. Park	Hanyang Univ.
	5-P22	Basic Study of Surface Treatment at Low Discharge Voltage by Atmospheric Microplasma	K. Shimizu	Shizuoka Univ.
			A. Umeda	Shizuoka Univ.
			M. Blajan	Shizuoka Univ.
	5-P24	Color Stability and High Efficiency White Phosphorescent Organic Light-Emitting Diodes with Proper Position of Phosphorescent Red Emitter	J.S. Park	Hongik Univ.
			J.H. Seo	Hongik Univ.
			J.R. Koo	Hongik Univ.
			B.M. Seo	Hongik Univ.
			K.H. Lee	Sungkyunkwan Univ.
			J.K. Park	Sungkyunkwan Univ.
			S.S. Yoon	Sungkyunkwan Univ.
			Y.K. Kim	Hongik Univ.
	5-P25	Improvement of CVD SiO_2 by SPA Plasma Treatment	T. Shiozawa	Tokyo Electron AT Ltd.
			D. Katayama	Tokyo Electron AT Ltd.
			D. Tamura	Tokyo Electron AT Ltd.
			Y. Kabe	Tokyo Electron AT Ltd.
			T. Kobayashi	Tokyo Electron AT Ltd.
			Y. Sato	Tokyo Electron AT Ltd.
			Y. Hirota	Tokyo Electron AT Ltd.
			N. Yamamoto	Tokyo Electron AT Ltd.
	5-P26	Green Phosphorescent Organic Light-Emitting Diodes with Simplified Device Architecture	J.H. Seo	Hongik Univ.
			Y.Y. Jin	Hongik Univ.
			E.Y. Choi	Hongik Univ.
			H.M. Kim	Hongik Univ.
			J.H. Kim	Hongik Univ.
			Y.K. Kim	Hongik Univ.
	5-P27	Highly Efficient Phosphorescent OLEDs using Red Emitting Ir(III) Complexes with Acetylated Phenylpyridine Ligands	K.H. Lee	Sungkyunkwan Univ.
			H.J. Kang	Sungkyunkwan Univ.
			J.K. Park	Sungkyunkwan Univ.
			S.J. Lee	Hongik Univ.
			J.H. Seo	Hongik Univ.
			Y.K. Kim	Hongik Univ.
			S.S. Yoon	Sungkyunkwan Univ.
	5-P28	Titanium Oxide Thin Films Prepared by Plasma Enhanced Atomic Layer Deposition using Remote ECR Plasma for OLED Devices	B.-W. Kang	Hanyang Univ.
			W.-S. Kim	Hanyang Univ.
			D.-Y. Moon	Hanyang Univ.
			J.-G. Park	Hanyang Univ.
			J.-W. Park	Hanyang Univ.
	5-P29	Efficient Solution-Processed Small Molecular Green Phosphorescent Organic Light-Emitting Diodes by Mixed the Polymer Host	Y.Y. Jin	Hongik Univ.
			J.H. Seo	Hongik Univ.
			H.M. Kim	Hongik Univ.
			E.Y. Choi	Hongik Univ.
			J.H. Kim	Hongik Univ.
			J.-T. Je	SFC Co.,Ltd.
			Y.K. Kim	Hongik Univ.
	5-P30	Synthesis and Electroluminescent Properties of Blue Fluorescent Bis(diarylaminophenyl)bianthryls for OLEDs	J.N. You	Sungkyunkwan Univ.
			K.H. Lee	Sungkyunkwan Univ.
			W.C. Lee	Sungkyunkwan Univ.
			J.S. Park	Hongik Univ.
			J.H. Seo	Hongik Univ.
			Y.K. Kim	Hongik Univ.
			S.S. Yoon	Sungkyunkwan Univ.
	5-P31	Interaction of Hydrogen Plasma with Nanodispersed Iron-Carbon Composites	A.A. Savitsky	Belarusian State Univ.
			V.B. Drozdovich	Belarusian State Technological Univ.
			V.V. Pan'kov	Belarusian State Univ.
			V.V. Zhylinski	Belarusian State Technological Univ.
			S.A. Zhdanok	State Insitution
	5-P32	Synthesis and Electroluminescence of an Ir-Complex with a Phosphino-benzoimidazole	D.H. Trinh	Inje Univ.
			G.-C. Choi	Dong A Univ.
			Y.-S. Kwon	Dong A Univ.

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			B.-J. Lee	Inje Univ.
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			N. Hayashi	Saga Univ.
			H. Kawasaki	Sasebo NCT.
			T. Ohshima	Sasebo NCT.
			Y. Suda	Sasebo NCT.
	5-P34	Decomposition of Second Order Structure of Proteins Using RF Oxygen Plasma	N. Hayashi	Saga Univ.
			S. Kitazaki	Saga Univ.
			R. Kawaguchi	Saga Univ.
			L. Hao	Saga Univ.
			M. Goto	Saga Univ.
	5-P35	Sterilization of Tube Inner Surface using Oxygen and Water Vapor Plasmas	S. Kitazaki	Saga Univ.
			N. Hayashi	Saga Univ.
	5-P36	Composition and Crystalline Properties of TiNi Thin Films Prepared by PLD under Vacuum and in Ambient Ar Gas	J.O. Cha	Kyung Hee Univ.
			I.H. Joong	Japan Advanced Inst. of Science and Technology
			J. Sakai	Japan Advanced Inst. of Science and Technology
			T.H. Nam	Gyeong Sang National Univ.
			J.S. Ahn	Kyung Hee Univ.
	5-P37	Improved Light Extraction Efficiency of GaN-Based Light Emitting Diodes using Al Doped ZnO Current Spreading Layers	B.H. Kong	Sungkyunkwan Univ.
			W.S. Han	Sungkyunkwan Univ.
			C.H. Woo	Sungkyunkwan Univ.
			Y.S. Bae	Sungkyunkwan Univ.
			H.K. Cho	Sungkyunkwan Univ.
			M.Y. Kim	Samsung Electro-Mechanics Co.
			R.J. Choi	Samsung Electro-Mechanics Co.
	5-P38	Ar / H2 Plasma Cleaning Effect on Electroless Ni Plating for Micro-Bump Formation	A. Ikeda	Kyushu Univ.
			K. Kajiwara	Kyushu Univ.
			N. Watanabe	Fukuoka Industry, Science and Technology Foundation
			T. Asano	Kyushu Univ.
	5-P39	Electrochemical Characterization of O2 Plasma Functionalized MWCNT Electrode for L. Pneumophila DNA Sensor	E.J. Park	Korea Univ.
			J.-Y. Lee	Korea Univ.
			J.H. Kim	Korea Univ.
			C.J. Lee	Korea Univ.
			N.K. Min	Korea Univ.
	5-P40	Synthesis of Carbon Nanoflakes by Radio-Frequency Sputtering and Their Field Emission Characteristics	W.-C. Shih	Tatung Univ.
			J.-M. Jeng	Tatung Univ.
			C.-W. Tsou	Tatung Univ.
			J.-T. Lo	Tatung Company
			H.-C. Chen	TamKang Univ.
			I.-N. Lin	TamKang Univ.
	5-P41	Enhancement Mechanisms of the Color Purity in Deep Blue Organic Light-Emitting Devices Fabricated Utilizing an Emitting Layer Containing Mixed Fluorescence and Phosphorescence Host Materials	H.S. Bang	Hanyang Univ.
			D.C. Choo	Hanyang Univ.
			T.W. Kim	Hanyang Univ.
			J.H. Seo	Hong-ik Univ.
			Y.K. Kim	Hong-ik Univ.
	5-P42	Electro-Optical Characteristics of a Pulse Driven Micro-Electrical Discharge Machining for Drilling of Hybrid CNT/Al2O3 Nanocomposites	C.-S. Ha	Pusan National Univ.
			D.-H. Kim	Pusan National Univ.
			H.-J. Lee	Pusan National Univ.
			H.J. Lee	Pusan National Univ.
			D.-Y. Lee	Applied Carbone Nano Technology Co., LTD.
			H.-S. Tak	Pusan National Univ.
			M.C. Kang	Pusan National Univ.
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			H. Sugiura	Nagoya Univ.
			T. Ishijima	Nagoya Univ.
			H. Toyoda	Nagoya Univ.
	5-P44	Beveling of Silicon Carbide Wafer by Plasma Etching Using Atmospheric-Pressure Plasma	Y. Sano	Osaka Univ.
			T. Kato	Osaka Univ.
			K. Yamamura	Osaka Univ.
			H. Mimura	Osaka Univ.
			S. Matsuyama	Osaka Univ.
			K. Yamauchi	Osaka Univ.
	5-P45	Improvement of Thickness Uniformity of SOI Layer by Numerically Controlled Sacrificial Oxidation using Atmospheric-Pressure Plasma with Electrode Array System	S. Kamisaka	Osaka Univ.
			Y. Sano	Osaka Univ.
			H. Mimura	Osaka Univ.
			S. Matsuyama	Osaka Univ.
			K. Yamauchi	Osaka Univ.
	5-P46	DBD Plasma Produced in a Closed Container Used for Bacterial inactivation	A.S. Chiper	Al. I. Cuza Univ.
			W. Chen	Technical Univ. of Denmark
			O. Mejlholm	Technical Univ. of Denmark
			P. Dalgaard	Technical Univ. of Denmark
			E. Stamate	Technical Univ. of Denmark
	5-P47	Effect of the Pulse Modulation Frequency on Silicon Etching using an Atmospheric-Pressure ICP Microjet	S. Tajima	Univ. of Tokyo
			S. Tsuchiya	Univ. of Tokyo
			T. Ichiki	Univ of Tokyo / Univ. of Tokyo-CNBI / JST-CREST
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			K. Juri	Kyoto Inst. Tech.
			T. Sakaguchi	Kyoto Inst. Tech.
			H. Kuriki	Kyoto Inst. Tech.
			A. Kamoi	Kyoto Inst. Tech.
			S. Hotta	Kyoto Inst. Tech.
	5-P49	Atomic Scale Etch Depth Control of III-V Compound Materials using Atomic Layer Etching	W.S. Lim	SAINT, Sungkyunkwan Univ.
			Y.Y. Kim	Sungkyunkwan Univ.
			B.J. Park	Sungkyunkwan Univ.
			G.Y. Yeom	SAINT, Sungkyunkwan Univ.
	5-P50	Analysis of Non-Thermal Plasma Deposited Zinc Oxide Thin Film	M.R. Mansur	Jeju National Univ.
			O.V. Penkov	Jeju National Univ.
			V.Y. Plaksin	Jeju National Univ.
			J.S. Beom	Jeju National Univ.
			J.H. Kim	Jeju National Univ.
			H.-J. Lee	Jeju National Univ.
	5-P51	Selective Growth Process and Formation Mechanism of Biexcitonic Zinc Dimmers	K. Obara	Kagoshima Univ.
			M. Hamasaki	Kagoshima Univ.
			M. Obara	Kagoshima Univ.
			M. Yamaguchi	Kagoshima Univ.
			M. Kuwayama	Kagoshima Univ.
			J. Kawabata	Kagoshima Univ.
			H. Manaka	Kagoshima Univ.
Wet Process and Reactions	5-P52	Thick Gate Oxide Integrity Degradation in Lithography and Wet Cleaning Process	H.-F. Su	Macronix International Company, Ltd.
			A.-C. Wei	Macronix International Company, Ltd.
			N.-T. Lian	Macronix International Company, Ltd.
			T. Yang	Macronix International Company, Ltd.
			K.-C. Chen	Macronix International Company, Ltd.
			C.-Y. Lu	Macronix International Company, Ltd.
	5-P53	Effect of Temperature/Humidity Treatment Conditions on Interfacial Adhesion Energy between Electroless-plated Ni and Polyimide	S.-C. Park	Andong National Univ.
			K.-J. Min	Andong National Univ.
			K.-H. Lee	Korea Inst. of Materials Science
			Y. Jeong	Korea Inst. of Materials Science
			Y.-B. Park	Andong National Univ.